Z0107NA0



4Q Triac

Rev. 2 — 22 March 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring enhanced noise immunity and direct interfacing to logic ICs and low power gate drivers.

1.2 Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

1.3 Applications

- General purpose low power motor control
- Home appliances

- Industrial process control
- Low power AC Fan controllers

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|--|--|-----|-----|------|------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 800 | V |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5 | - | - | 12.5 | Α |
| I _{T(RMS)} | RMS on-state current | full sine wave; T _{lead} ≤ 45 °C; see <u>Figure 1</u> ; see <u>Figure 3</u> ; see <u>Figure 2</u> | - | - | 1 | Α |



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Table 1. Quick reference data ...continued

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------------------|-------------------------|---|-----|-----|-----|------|
| Static cha | aracteristics | | | | | |
| I _{GT} gate trig current | gate trigger current | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ or } T}$ | 0.3 | - | 5 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ or } T_j}$ | 0.3 | - | 5 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;} $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ or } T}$ | 0.3 | - | 5 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$ | 0.3 | - | 7 | mA |

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|------|--------|-----------------|--------------------|-----------------|
| FIII | Symbol | Description | Simplified oddine | Grapinic Symbol |
| 1 | T2 | main terminal 2 | | L I |
| 2 | G | gate | | T2—T1 |
| 3 | T1 | main terminal 1 | | Sym051 |
| | | | SOT54 (TO-92) | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|---|---------|
| | Name | Description | Version |
| Z0107NA0 | TO-92 | plastic single-ended leaded (through hole) package; 3 leads | SOT54 |

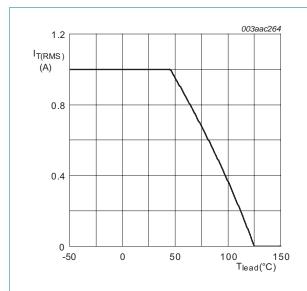
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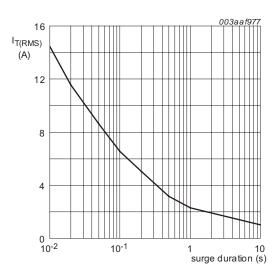
4. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|---|-----|------|--------|
| V_{DRM} | repetitive peak off-state voltage | | - | 800 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; T _{lead} ≤ 45 °C; see <u>Figure 1</u> ; see <u>Figure 3</u> ; see <u>Figure 2</u> | - | 1 | Α |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5 | - | 12.5 | Α |
| | | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$ | - | 13.8 | Α |
| l ² t | I ² t for fusing | t _p = 10 ms; sine-wave pulse | - | 0.78 | A^2s |
| dI _T /dt | rate of rise of on-state current | $I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 100 \text{ mA/}\mu\text{s}$; T2+ G+ | - | 50 | A/µs |
| | | $I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 100 \text{ mA/}\mu\text{s}$; T2+ G- | - | 50 | A/µs |
| | | $I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 100 \text{ mA/}\mu\text{s}$; T2- G- | - | 50 | A/µs |
| | | $I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 100 \text{ mA/}\mu\text{s}$; T2- G+ | - | 20 | A/µs |
| I _{GM} | peak gate current | | - | 1 | Α |
| P _{GM} | peak gate power | | - | 2 | W |
| P _{G(AV)} | average gate power | over any 20 ms period | - | 0.1 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| Tj | junction temperature | | - | 125 | °C |

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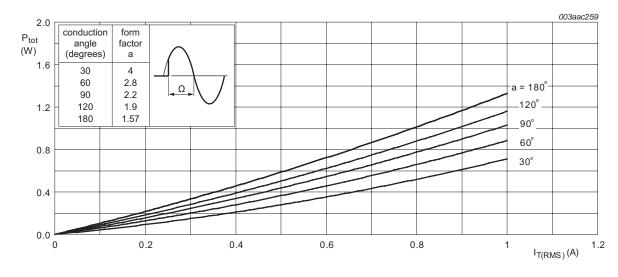




f = 50Hz, $T_{lead} = 45$ °C

Fig 1. RMS on-state current as a function of lead temperature; maximum values

Fig 2. RMS on-state current as a function of surge duration; maximum values



 α = conduction angle

Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

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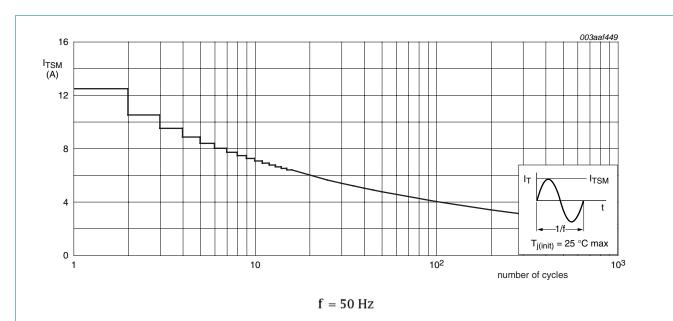
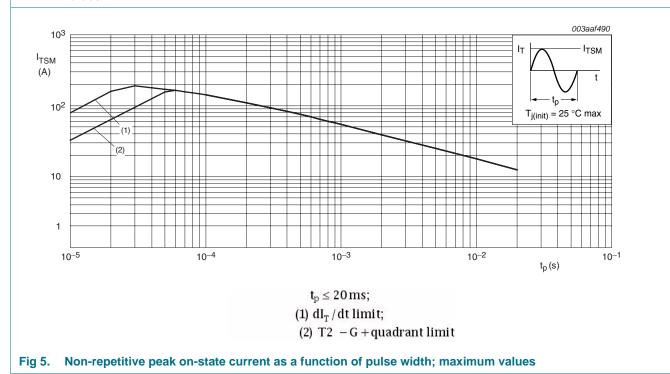


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



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Thermal characteristics

Table 5. **Thermal characteristics**

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------------|---|---|-----|-----|-----|------|
| $R_{\text{th(j-lead)}}$ | thermal resistance from junction to lead | full cycle; see Figure 6 | - | - | 60 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | full cycle; printed circuit board mounted; lead length 4 mm | - | 150 | - | K/W |

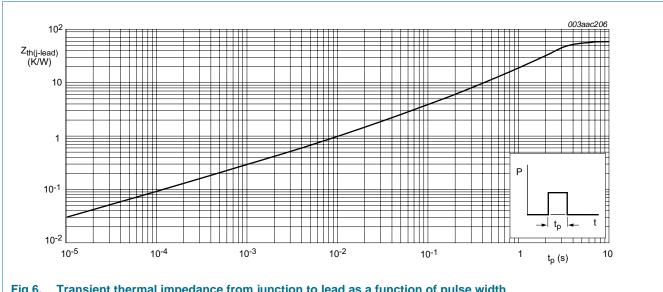


Fig 6. Transient thermal impedance from junction to lead as a function of pulse width

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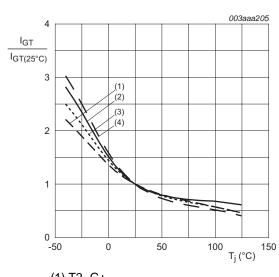
6. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|--|-----|-----|-----|------|
| Static cha | racteristics | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$ | 0.3 | - | 5 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$ | 0.3 | - | 5 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 7}}{}$ | 0.3 | - | 5 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$ | 0.3 | - | 7 | mA |
| L | latching current | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$ | - | - | 10 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 8}}{}$ | - | - | 25 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 8}}{\text{C}}$ | - | - | 10 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 8}}{\text{C}}$ | - | - | 10 | mA |
| Н | holding current | $V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$ | - | - | 10 | mΑ |
| √ _T | on-state voltage | I _T = 1 A; T _j = 25 °C; see <u>Figure 10</u> | - | 1.3 | 1.6 | V |
| V_{GT} | gate trigger voltage | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> | - | - | 1.3 | V |
| | | $V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see <u>Figure 11</u> | 0.2 | - | - | V |
| D | off-state current | V _D = 800 V; T _j = 125 °C | - | - | 0.5 | mΑ |
| Dynamic | characteristics | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 536 V; T_j = 110 °C; gate open circuit; exponential waveform; see Figure 12 | 100 | - | - | V/µs |
| dV _{com} /dt | rate of change of commutating voltage | $V_D = 400 \text{ V}; T_j = 110 ^{\circ}\text{C};$ $dl_{com}/dt = 0.44 \text{ A/ms}; \text{ gate open circuit}$ | 0.5 | - | - | V/µs |

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig 7. Normalized gate trigger current as a function of junction temperature

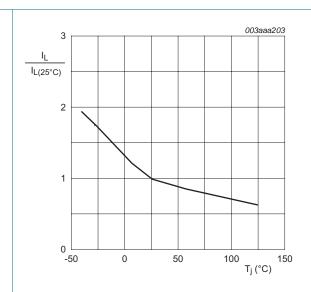


Fig 8. Normalized latching current as a function of junction temperature

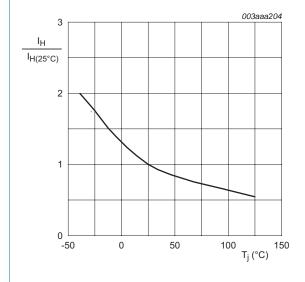
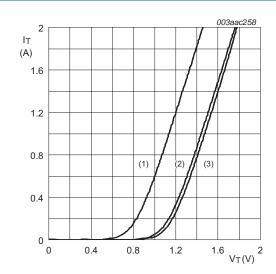


Fig 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$

 $R_s = 0.31 \Omega$

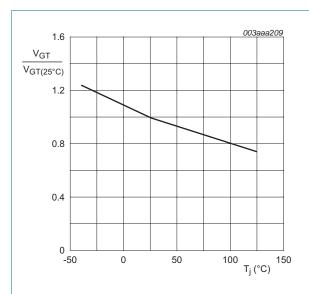
(1) T_j = 125 °C; typical values

(2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage

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1.6
A
1.2
0.8
0.4
0.4 $0 = \frac{dV_D/dt}{dV_{D(25^{\circ}\text{C})}/dt}$

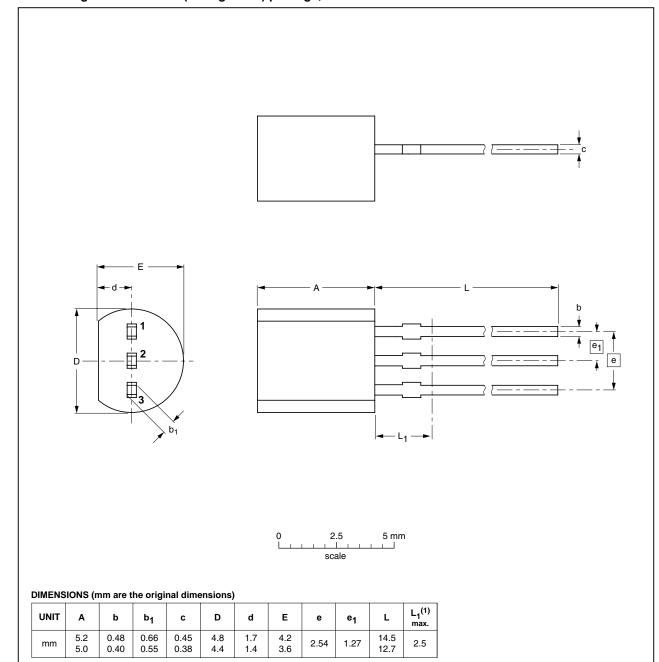
Fig 11. Normalized gate trigger voltage as a function of junction temperature

Fig 12. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

7. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

| OUTLINE | | REFER | ENCES | EUROPEAN | ISSUE DATE |
|---------|-----|-------|--------|------------|----------------------------------|
| VERSION | IEC | JEDEC | JEITA | PROJECTION | ISSUE DATE |
| SOT54 | | TO-92 | SC-43A | | -04-06-28 04-11-16 |

Fig 13. Package outline SOT54 (TO-92)

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8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|-----------------------------------|--------------------|---------------|--------------|
| Z0107NA0 v.2 | 20110322 | Product data sheet | - | Z0107NA0 v.1 |
| Modifications: | Various chang | ges to content. | | |
| Z0107NA0 v.1 | 20110103 | Product data sheet | - | - |

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9. Legal information

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| Document status [1] [2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
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| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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